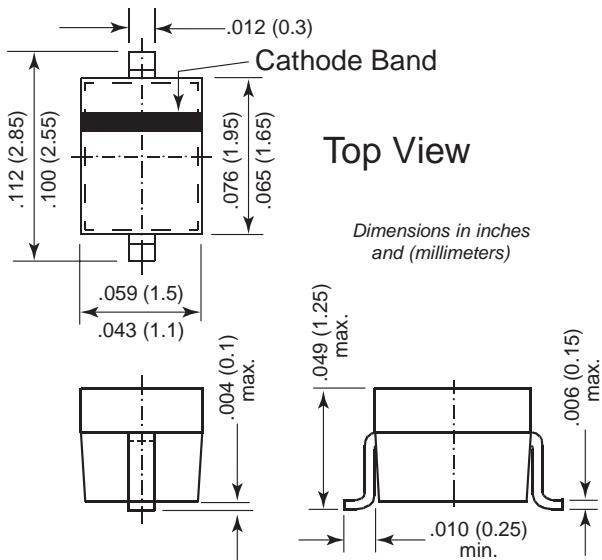



**SOD-323**


## Features

- For general purpose applications.
- The SD103 series is a metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring.
- The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing, and coupling diodes for fast switching and low logic level applications.
- This diode is also available in the MiniMELF case with the type designations LL103A to LL103C, DO-35 case with the type designations SD103A to SD103C and SOD-123 case with type designations SD103AW to SD103CW.

## Mechanical Data

**Case:** SOD-323 plastic case

**Weight:** approximately 0.004g

**Marking** SD103AWS = S6

**Code:** SD103BWS = S7

SD103CWS = S8

### Packaging Codes/Options:

D5/10K per 13" reel (8mm tape), 30K/box  
 D6/3K per 7" reel (8mm tape), 30K/box

## Maximum Ratings and Thermal Characteristics (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Peak Inverse Voltage	SD103AWS SD103BWS SD103CWS	V <sub>RRM</sub>	40 30 20	V
Power Dissipation (Infinite Heat Sink)		P <sub>tot</sub>	150 <sup>(1)</sup>	mW
Maximum Single Cycle Surge 10μs Square Wave		I <sub>FSM</sub>	2	A
Thermal Resistance Junction to Ambient Air		R <sub>θJA</sub>	650 <sup>(1)</sup>	°C/W
Junction Temperature		T <sub>j</sub>	125 <sup>(1)</sup>	°C
Storage Temperature Range		T <sub>s</sub>	-55 to +150 <sup>(1)</sup>	°C

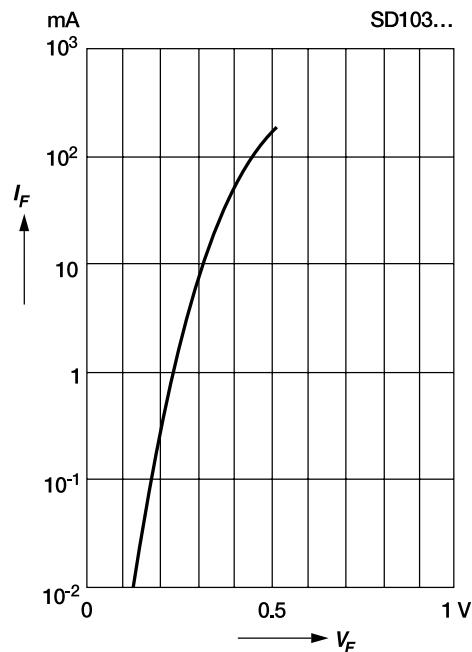
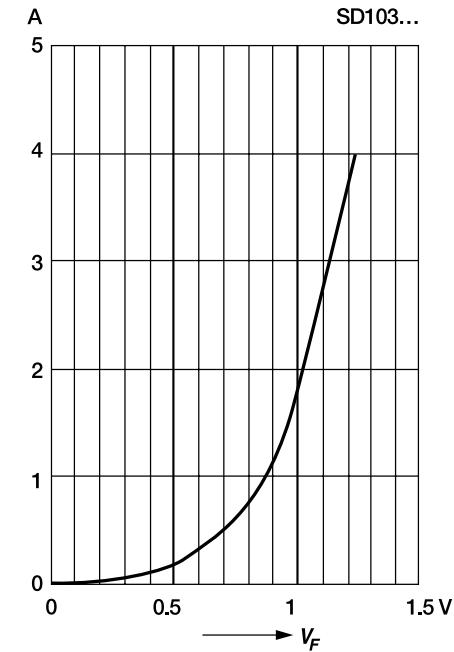
**Note:**

(1) Valid provided that electrodes are kept at ambient temperature

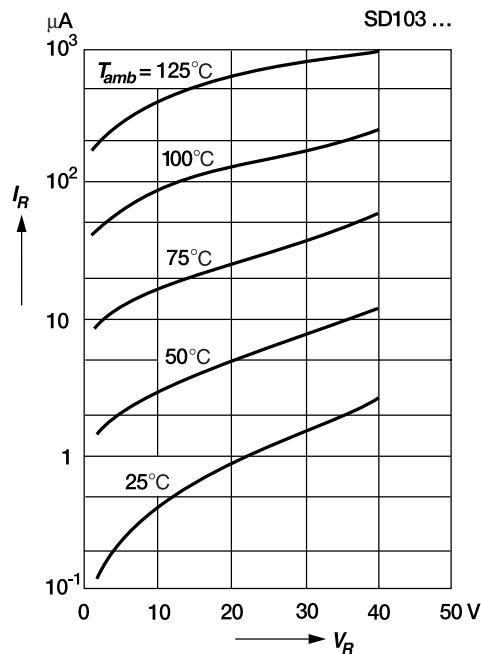
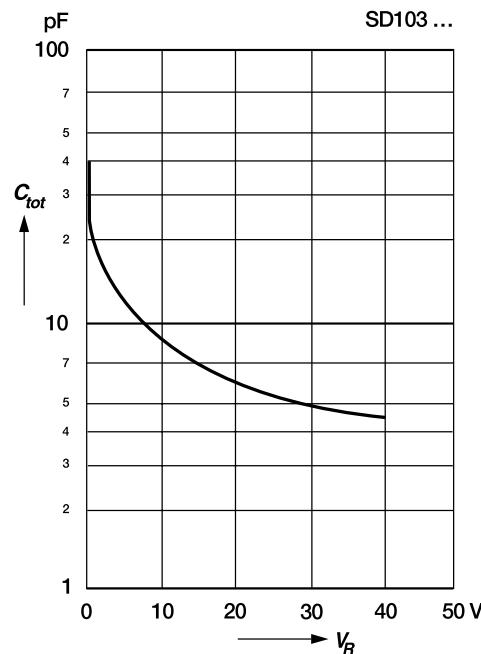
**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Leakage Current SD103AWS SD103BWS SD103CWS	$I_R$	$V_R = 30\text{V}$	—	—	5	
		$V_R = 20\text{V}$	—	—	5	
		$V_R = 10\text{V}$	—	—	5	
Forward Voltage Drop	$V_F$	$I_F = 20\text{mA}$ $I_F = 200\text{mA}$	—	—	0.37 0.6	V
Junction Capacitance	$C_{tot}$	$V_R = 0\text{V}$ $f = 1\text{MHz}$	—	50	—	pF
Reverse Recovery Time	$t_{rr}$	$I_F = I_R = 50\text{mA}$ to $200\text{mA}$ recover to $0.1I_R$	—	10	—	ns

**Ratings and  
Characteristic Curves** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

**Typical variation of fwd. current  
vs. fwd. voltage for primary conduction  
through the Schottky barrier**

**Typical high current forward  
conduction curve  
 $t_p = 300$  ms, duty cycle = 2%**


**Ratings and  
Characteristic Curves** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

**Typical variation of reverse current  
at various temperatures**

**Typical capacitance  
versus reverse voltage**

**Blocking voltage deration  
versus temperature at various  
average forward currents**
